

# Corrections to “Experimental Study of Adversarial Magnetic Field Exposure Attacks on Toggle MRAM Chips”

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In the above article [1], the magnetic field strength mentioned was “700 KGauss.” The occurrence of “K” in the units is an inadvertent, unintentional typographical error. The correct value must be “700 Gauss” in the last sentence of Section III-A and in the captions of [Figs. 5–11](#).

## REFERENCES

- [1] S. Chakraborty and M. Suri, “Experimental study of adversarial magnetic field exposure attacks on toggle MRAM chips,” *IEEE Trans. Electron Devices*, vol. 69, no. 3, pp. 1480–1485, Mar. 2022, doi: [10.1109/TED.2022.3146222](https://doi.org/10.1109/TED.2022.3146222).

Manuscript received 7 December 2022; accepted 8 December 2022.  
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Digital Object Identifier 10.1109/TED.2022.3230319